PATENT APPLICATION

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FORM	PTO-1449	

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION	NO.
10007286-1	09/975,297		
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REFERENCE DESIGNATION

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

M	10	G.G.P. van GORKOM et al., "Performance of Silicon Cold Cathodes", September 30, 1985, J. Vac. Sci. Technol. B 4(1), Jan/Feb 1986, pp. 108-111.
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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

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PATENT APPLICATION

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

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ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION	NO.
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